PATENT ABSTRACTS OF JAPAN

(11)Publication number:

2002-231780

(43) Date of publication of application: 16.08.2002

(51)Int.CI.

H01L 21/66 G01N 27/00

H01L 21/28 H01L 21/768

(21)Application number : 2001-021615

(71)Applicant: JEOL LTD

(22)Date of filing:

30.01.2001

(72)Inventor: KIKUCHI MAKI

NEGISHI TSUTOMU

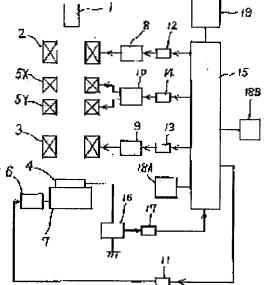
ONO MIYUKI

(54) METHOD FOR INSPECTING HOLE BY USING CHARGED PARTICLE BEAM

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a method for inspecting the etching state of a contact hole or a via hole.

SOLUTION: Electron beams are sequentially irradiated to a contact hole formed on a sample like a wafer, and an absorption current flowing in the sample 4 is detected by a current amplifier 16, and obtained absorption current signal data is stored in a memory 18. A controller £ 15 checks the absorption current signal data up in a relation between a current flowing between the sample and a ground to be acquired in advance by use of a standard sample and an etching depth of a substrate in the contact hole, and inspects the etching depth of the substrate in a hole to be measured.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of

rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]